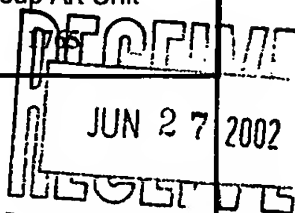
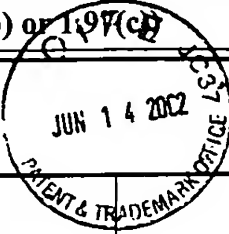


GAU 1765

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT (Under 37 CFR 1.97(b) or 1.97(c))			Docket No. 08228/019001	
In Re Application Of: Shiro SAKAI et al.				
Serial No. 10/044,686	Filing Date January 11, 2002	Examiner	Group Art Unit	
Title: NITRIDE SEMICONDUCTOR CHIP AND METHOD FOR MANUFACTURING NITRIDE SEMICONDUCTOR CHIP				
<div style="text-align: center;"> <p>Address to:</p> <p>Assistant Commissioner for Patents</p> <p>Washington, D.C. 20231</p> </div> <div style="text-align: center; margin-top: 20px;"> <p>37 CFR 1.97(b)</p> <p>1. <input checked="" type="checkbox"/> The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application; within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; or before the mailing date of a first Office Action on the merits, whichever event occurs last.</p> <p style="text-align: center; margin-top: 20px;">37 CFR 1.97(c)</p> <p>2. <input type="checkbox"/> The Information Disclosure Statement submitted herewith is being filed after three months of the filing of a national application, or the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; or after the mailing date of a first Office Action on the merits, whichever occurred last but before the mailing date of either:</p> <div style="margin-left: 40px;"> <p>1. a Final Action under 37 CFR 1.113, or</p> <p>2. a Notice of Allowance under 37 CFR 1.311,</p> <p>whichever occurs first.</p> </div> <p>Also submitted herewith is:</p> <div style="margin-left: 40px;"> <p><input type="checkbox"/> a certification as specified in 37 CFR 1.97(e);</p> <p style="text-align: center; margin-top: 10px;">OR</p> <p><input type="checkbox"/> the fee set forth in 37 CFR 1.17(p) for submission of an Information Disclosure Statement under 37 CFR 1.97(c).</p> </div> </div>				



COPY OF PAPERS
ORIGINALLY FILED

RECEIVED
JUN 18 2002
TC 1700

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT
(Under 37 CFR 1.97(b) or 1.97(c))

Docket No.
08228/019001

In Re Application Of: Shiro SAKAI et al.

Serial No.
10/044,686

Filing Date
January 11, 2002

Examiner

Group Art Unit
1765

Title: NITRIDE SEMICONDUCTOR CHIP AND METHOD FOR MANUFACTURING NITRIDE
SEMICONDUCTOR CHIP

Payment of Fee

(Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))

- ☐ A check in the amount of _____ is attached.
- ☒ The Assistant Commissioner is hereby authorized to charge and credit Deposit Account No. 50-0591 as described below. A duplicate copy of this sheet is enclosed.
- ☐ Charge the amount of _____
- ☐ Credit any overpayment.
- ☒ Charge any additional fee required.

Certificate of Transmission by Facsimile*

I certify that this document and authorization to charge deposit account is being facsimile transmitted to the United States Patent and Trademark Office (Fax. No. _____)

on _____
(Date)

Signature

Typed or Printed Name of Person Signing Certificate

Certificate of Mailing by First Class Mail

I certify that this document and fee is being deposited on 6/6/02 with the U.S. Postal Service as first class mail under 37 C.F.R. 1.8 and is addressed to the Assistant Commissioner for Patents, Washington, D.C. 20231.

Signature of Person Mailing Correspondence

Tawana L. Garcia

Typed or Printed Name of Person Mailing Correspondence

*This certificate may only be used if paying by deposit account.

Jonathan P. Osha, Reg. No. 33,986
ROSENTHAL & OSHA L.L.P.
1221 McKinney Street, Suite 2800
Houston, Texas 77010

Telephone: 713-228-8600
Facsimile: 713-228-8778

Dated: 6/6/02

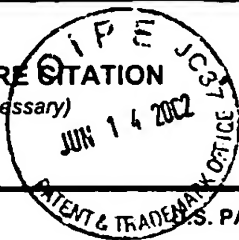
COPY OF PAPERS
ORIGINALLY FILED

RECEIVED
JUN 18 2002
TC 1700

CC:

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)



ATTY DOCKET NO.

08228/019001

SERIAL NO.

10/044,686

Shiro SAKAI et al.

FILING

January 11, 2002

GROUP

1765

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	A1	5,332,697	07/26/1994	Smith et al.	437	242	10/16/1991
	A2	6,090,666	07/18/2000	Ueda et al.	438	257	09/30/1998

COPY OF PAPERS
ORIGINALLY FILED

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	A3	EP 0 942 459 A1	09/15/1999	Europe				
	A4	EP 0 779 666 A2	06/18/1997	Europe				
	A5	11-111867	04/23/1999	Japan				✓

RECEIVED
JUN 18 2002
TC 1700

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	A6	Patent Abstracts of Japan, Publication No. 11111867, Publication Date 04/23/1999, 1 page
	A7	"Drastic Reduction of the Dislocation Density in GaN Films by Anti-Surfactant-Mediated Dot Formation"; M. TAKEUCHI et al., Workbook, The Tenth International Conference on Metalorganic Vapor Phase Epitaxy, June 5-9, 2000, Hokkaido University Conference Hall, Sapporo, Japan, 3 pages

EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

